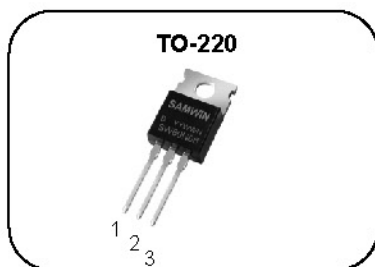


## N-channel TO-220 MOSFET

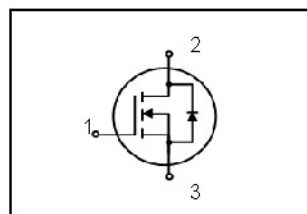
### Features

- High ruggedness
- $R_{DS(ON)}$  (Max8.5m $\Omega$ )@ $V_{GS}=10V$
- Gate Charge (Typical 72nC)
- Improved dv/dt Capability
- 100% Avalanche Tested



1. Gate 2. Drain 3. Source

$BV_{DSS}$  : 80V  
 $I_D$  : 80A  
 $R_{DS(ON)}$  : 8.5m $\Omega$



### General Description

This power MOSFET is produced with advanced VDMOS technology of SAMWIN. This technology enable power MOSFET to have better characteristics, such as fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics. This power MOSFET is usually used at high efficient DC to DC converter block and switch mode power supply.

### Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW P 80N08	SW80N08B	TO-220	TUBE

### Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{DSS}$	Drain to Source Voltage	80	V
$I_D$	Continuous Drain Current (@ $T_C=25^{\circ}C$ )	80*	A
	Continuous Drain Current (@ $T_C=100^{\circ}C$ )	50.4*	A
$I_{DM}$	Drain current pulsed (note 1)	320	A
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$E_{AS}$	Single pulsed Avalanche Energy (note 2)	390	mJ
$E_{AR}$	Repetitive Avalanche Energy (note 1)	64	mJ
dv/dt	Peak diode Recovery dv/dt (note 3)	5	V/ns
$P_D$	Total power dissipation (@ $T_C=25^{\circ}C$ )	173.6	W
	Derating Factor above 25 $^{\circ}C$	1.4	W/ $^{\circ}C$
$T_{STG}, T_J$	Operating Junction Temperature & Storage Temperature	-55 ~ + 150	$^{\circ}C$
$T_L$	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.	300	$^{\circ}C$

\*. Drain current is limited by junction temperature.

### Thermal characteristics

Symbol	Parameter	Value	Unit
$R_{thjc}$	Thermal resistance, Junction to case	0.72	$^{\circ}C/W$
$R_{thcs}$	Thermal resistance, Case to Sink		$^{\circ}C/W$
$R_{thja}$	Thermal resistance, Junction to ambient	53.1	$^{\circ}C/W$

Electrical characteristic (  $T_C = 25^\circ\text{C}$  unless otherwise specified )

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
<b>Off characteristics</b>						
$BV_{DSS}$	Drain to source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	80			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown voltage temperature coefficient	$I_D=250\mu A$ , referenced to $25^\circ\text{C}$		0.07		$V/^\circ\text{C}$
$I_{DSS}$	Drain to source leakage current	$V_{DS}=80V, V_{GS}=0V$			1	$\mu A$
		$V_{DS}=64V, T_C=125^\circ\text{C}$			50	$\mu A$
$I_{GSS}$	Gate to source leakage current, forward	$V_{GS}=20V, V_{DS}=0V$			100	nA
	Gate to source leakage current, reverse	$V_{GS}=-20V, V_{DS}=0V$			-100	nA
<b>On characteristics</b>						
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
$R_{DS(ON)}$	Drain to source on state resistance	$V_{GS}=10V, I_D=40A$		6.7	8.5	m $\Omega$
$G_{fs}$	Forward Transconductance	$V_{DS}=15V, I_D=30A$		90		S
<b>Dynamic characteristics</b>						
$C_{iss}$	Input capacitance	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$		6620		pF
$C_{oss}$	Output capacitance			496		
$C_{rss}$	Reverse transfer capacitance			222		
$t_{d(on)}$	Turn on delay time	$V_{DS}=40V, I_D=70A, R_G=25\Omega$ (note 4, 5)		28		ns
$t_r$	Rising time			72		
$t_{d(off)}$	Turn off delay time			169		
$t_f$	Fall time			119		
$Q_g$	Total gate charge	$V_{DS}=64V, V_{GS}=10V, I_D=70A$ (note 4, 5)		72		nC
$Q_{gs}$	Gate-source charge			17		
$Q_{gd}$	Gate-drain charge			29		

## Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			80	A
$I_{SM}$	Pulsed source current				320	A
$V_{SD}$	Diode forward voltage drop.	$I_S=80A, V_{GS}=0V$			1.5	V
$T_{rr}$	Reverse recovery time	$I_S=70A, V_{GS}=0V,$ $dI_f/dt=100A/\mu s$		18		ns
$Q_{rr}$	Reverse recovery Charge			12		nC

※. Notes

1. Repetitive rating : pulse width limited by junction temperature.
2.  $L = 0.87\text{mH}, I_{AS} = 30A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 70A, di/dt = 100A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature.

Fig. 1. On-state characteristics

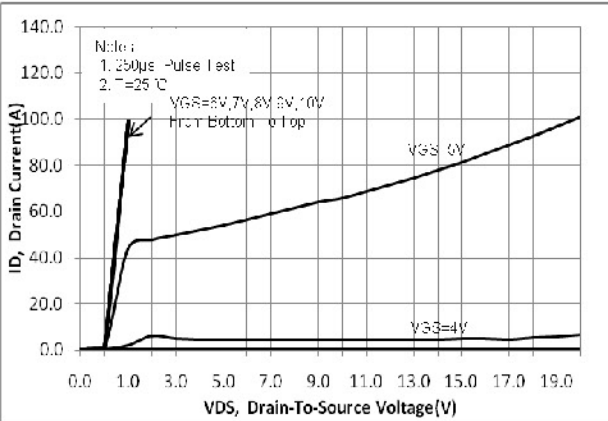


Fig. 2. On-resistance variation vs. drain current and gate voltage

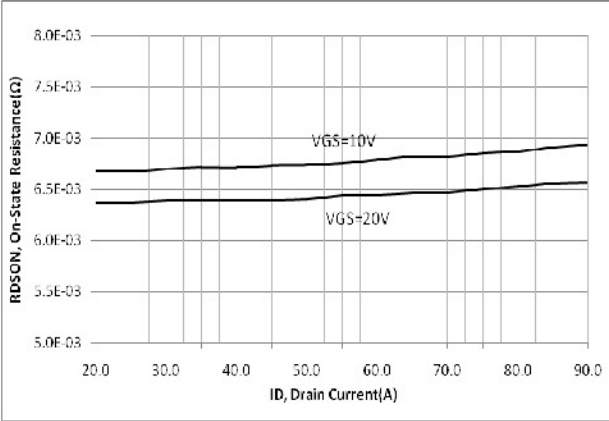


Fig. 3. Gate charge characteristics

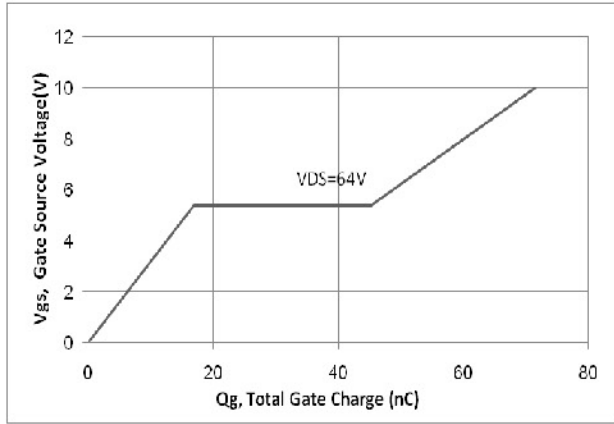


Fig. 4. On state current vs. diode forward voltage

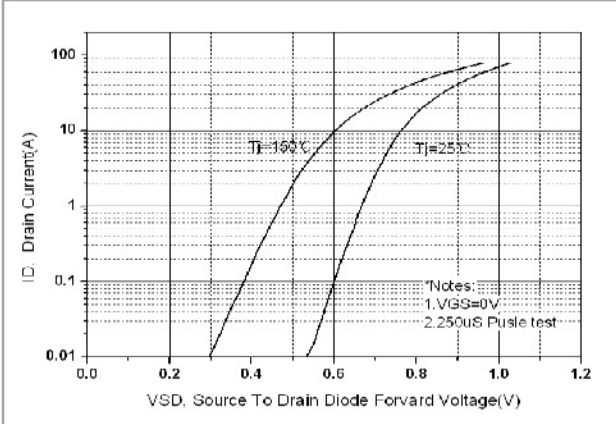


Fig 5. Breakdown Voltage Variation vs. Junction Temperature

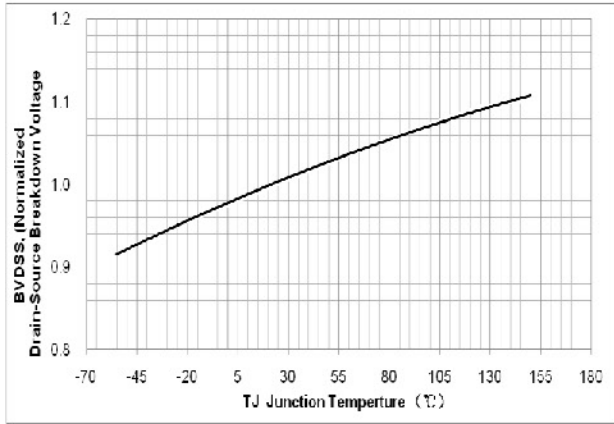


Fig. 6. On resistance variation vs. junction temperature

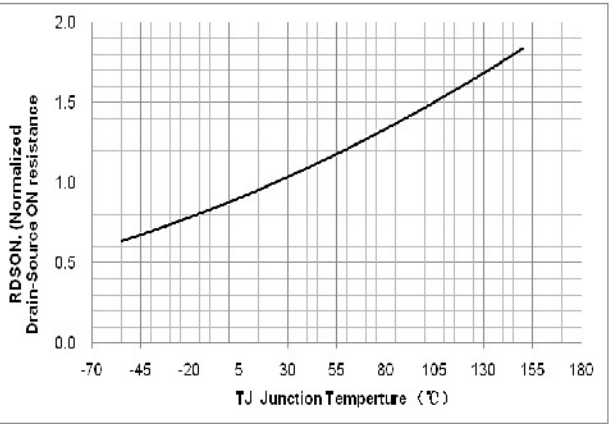


Fig. 7. Maximum safe operating area

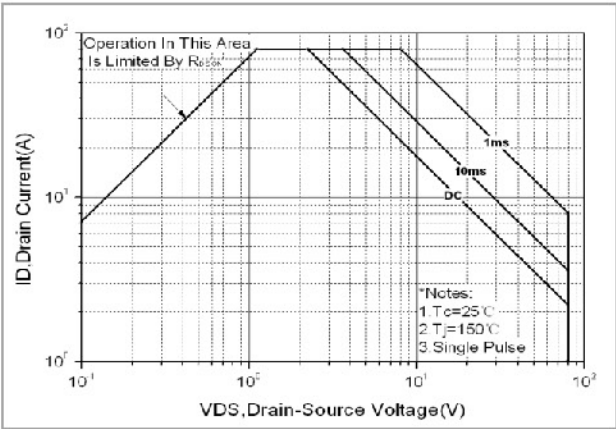


Fig. 8. Transient thermal response curve

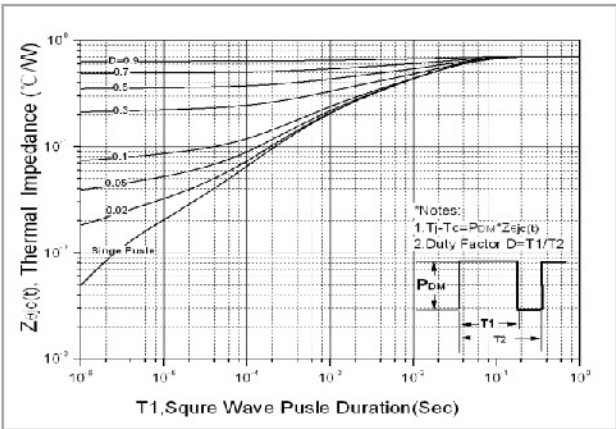


Fig. 9. Capacitance Characteristics

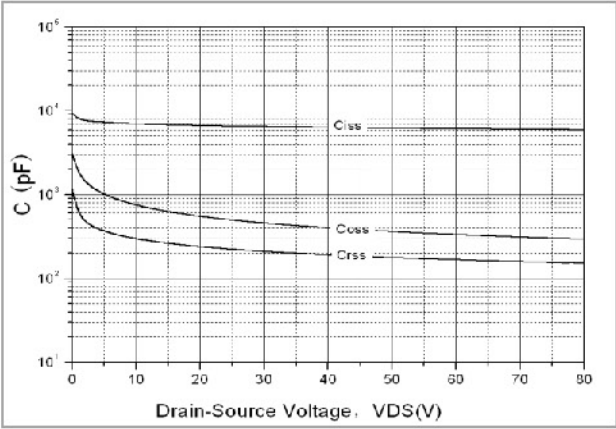


Fig. 10. Gate charge test circuit & waveform

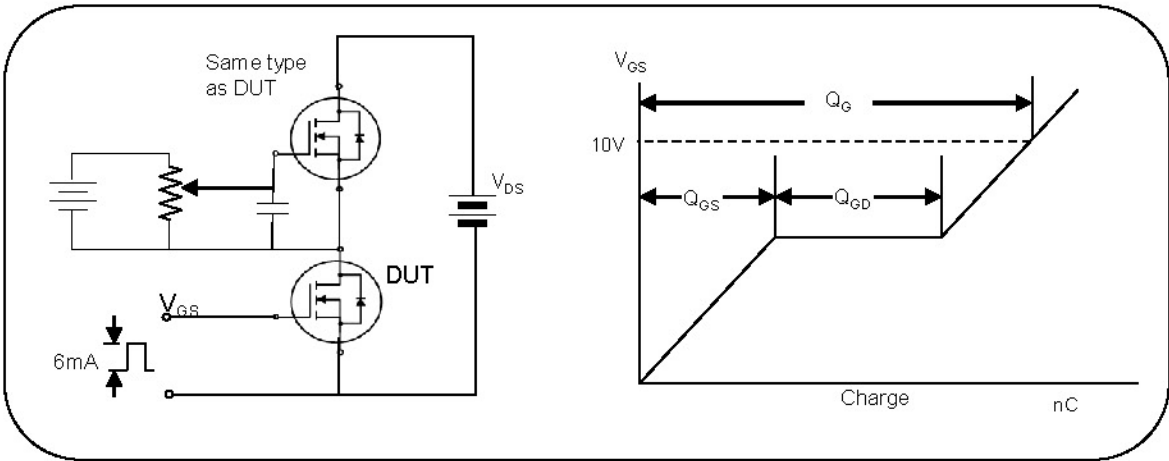


Fig. 11. Switching time test circuit & waveform

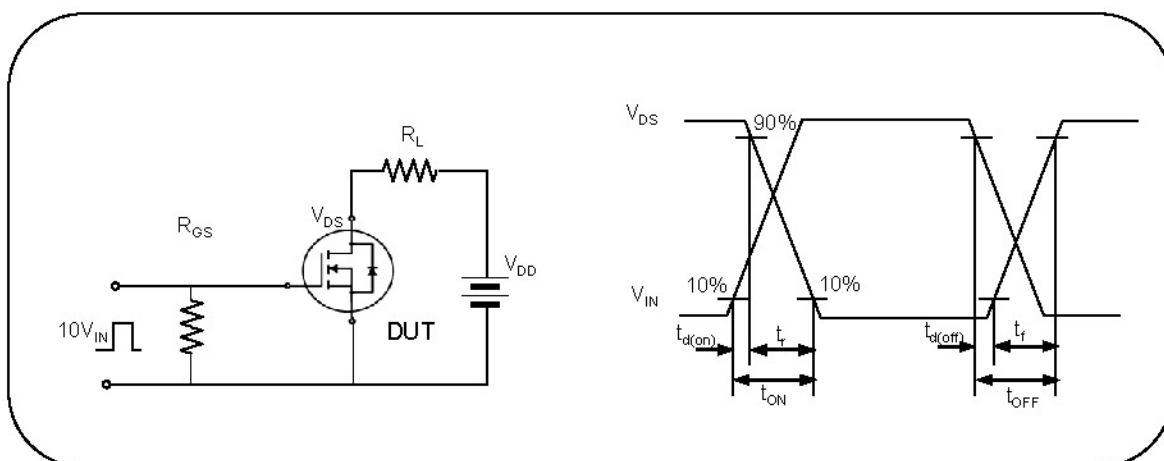


Fig. 12. Unclamped Inductive switching test circuit & waveform

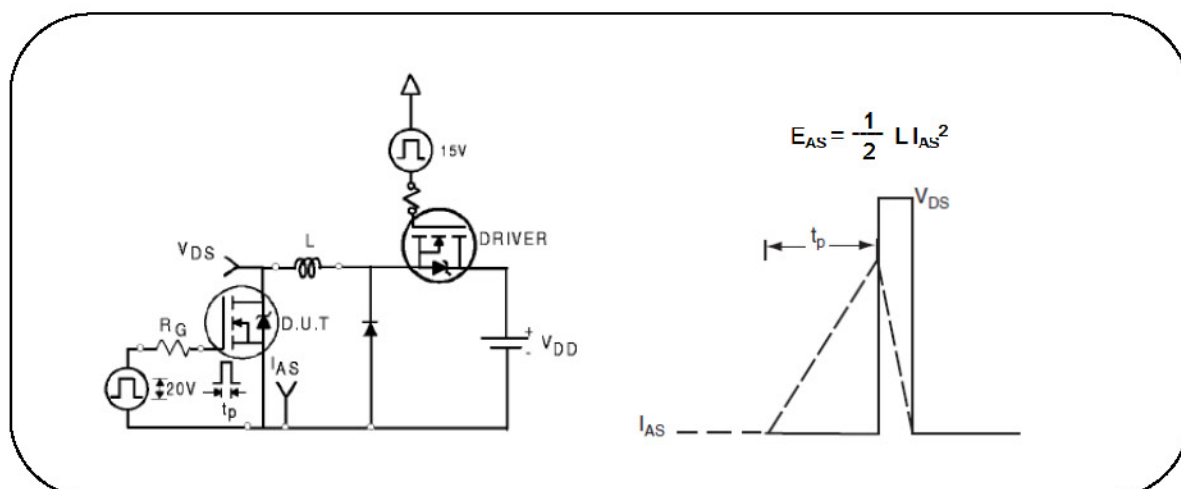


Fig. 13. Peak diode recovery dv/dt test circuit & waveform

